FIG. 1

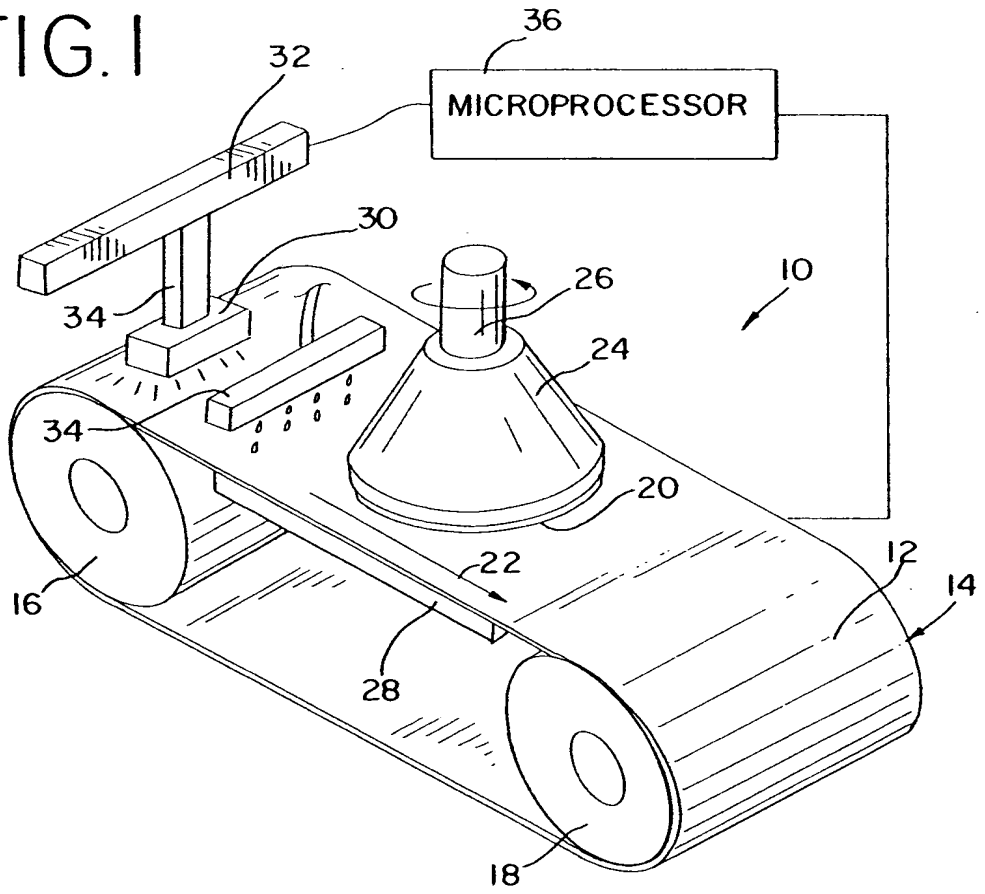

36
MICROPROCESSOR
32
30
34
26
10
24
34
20
22
12
14
16
28
18

FIG. 2

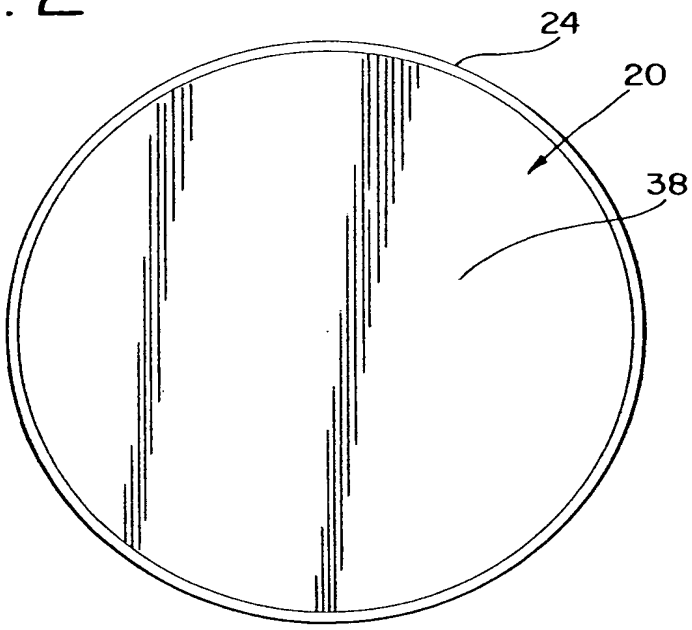

24
20
38

FIG. 3

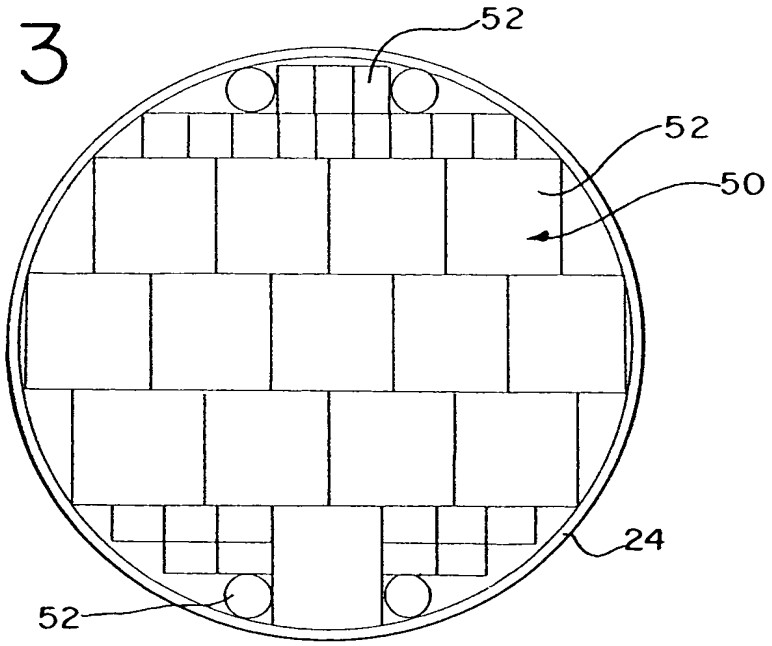

52
52
50
24
52

FIG. 4

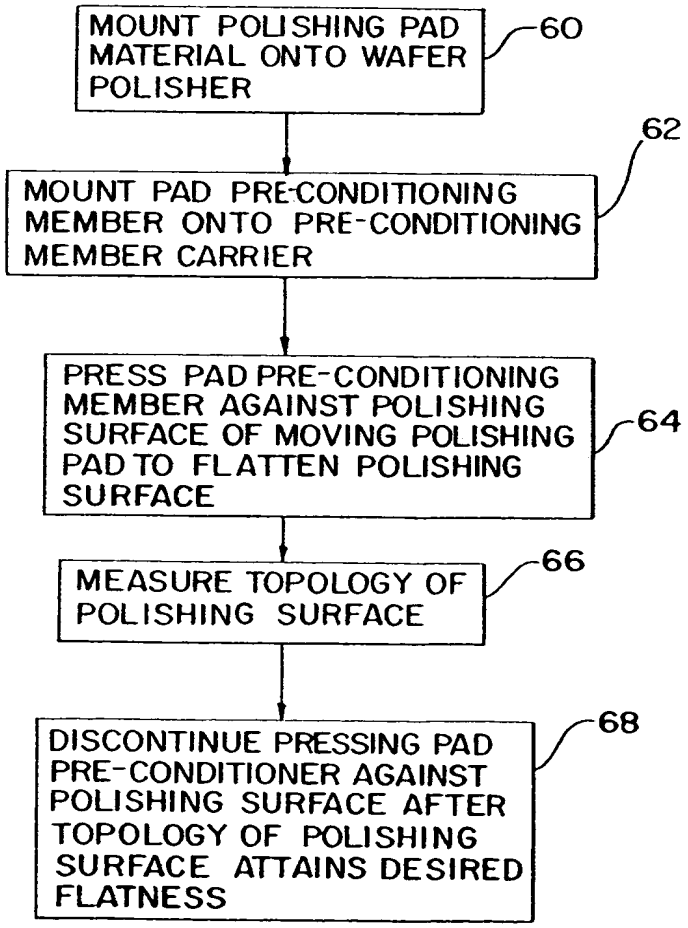
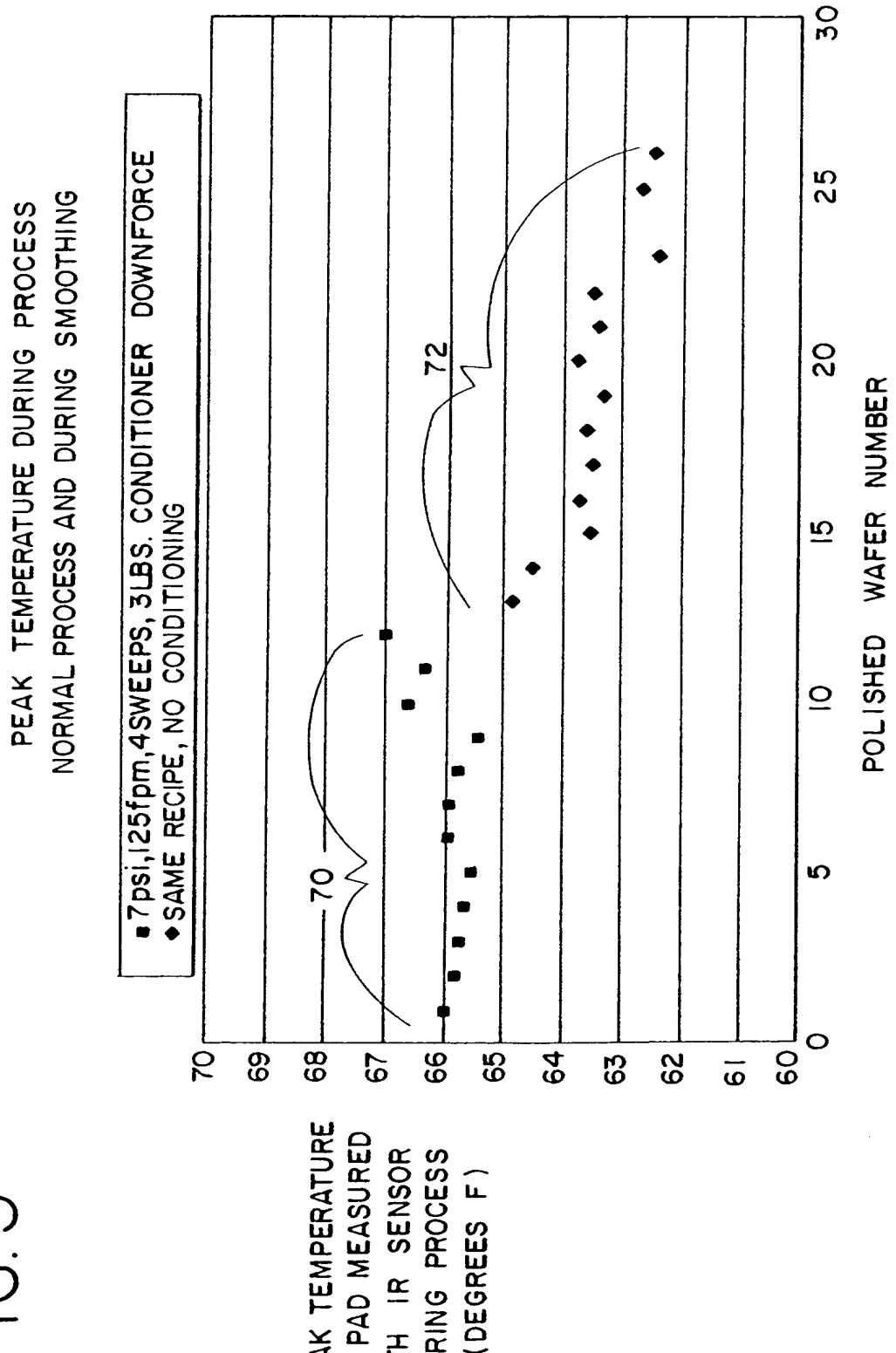

MOUNT POLISHING PAD MATERIAL ONTO WAFER POLISHER
60
MOUNT PAD PRE-CONDITIONING MEMBER ONTO PRE-CONDITIONING MEMBER CARRIER
62
PRESS PAD PRE-CONDITIONING MEMBER AGAINST POLISHING SURFACE OF MOVING POLISHING PAD TO FLATTEN POLISHING SURFACE
64
MEASURE TOPOLOGY OF POLISHING SURFACE
66
DISCONTINUE PRESSING PAD PRE-CONDITIONER AGAINST POLISHING SURFACE AFTER TOPOLOGY OF POLISHING SURFACE ATTAINS DESIRED FLATNESS
68

FIG. 5


PEAK TEMPERATURE DURING PROCESS
NORMAL PROCESS AND DURING SMOOTHING
■ 7psi, 125fpm, 4SWEEPS, 3LBS. CONDITIONER DOWNFORCE
◆ SAME RECIPE, NO CONDITIONING
70
72
PEAK TEMPERATURE OF PAD MEASURED WITH IR SENSOR DURING PROCESS (DEGREES F)
70
69
68
67
66
65
64
63
62
61
60
0
5
10
15
20
25
30
POLISHED WAFER NUMBER